Inel-6080 VLSI Systems Design Design Rules for CMOS

Lecture 7

Electrical and Computer Engineering Department University of Puerto Rico at Mayagüez

Fall 2008

Design Rules

- Allow for a ready translation of a circuit concept into an actual geometry in silicon
- Provide a set of guidelines for constructing the fabrication masks
 - Minimum line width
 - Minimum spacing between objects
- Multiple design rule specification methods exist
 - Scalable Design Rules (Lambda rules)
 - Micron Rules

Specifying Design Rules

Lambda Rules:

- Expressed in terms of a scaling parameter: Lambda (λ)
- Minimum line width: 2λ
- Main disadvantages:
 - Limited linear scaling
 - Too conservative

Micron Rules

- Express designs in absolute dimensions
- Pro: Allow taking full advantage of technology
- Con: Scaling and Porting becomes more complicated

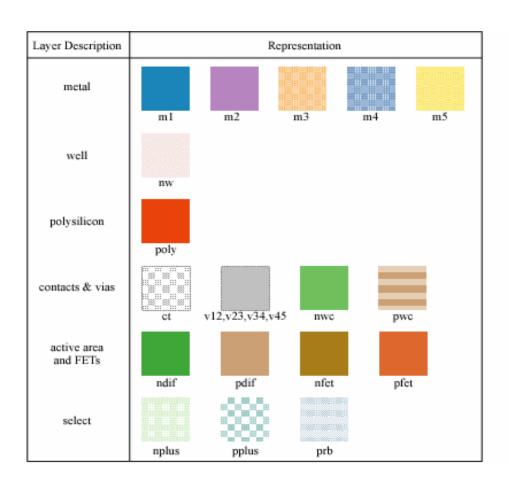
Design Rule Entities

- 1. Layer Representations
 - Substrates and/or Wells
 - Diffusion Regions (Active areas)
 - Select regions: For contacts to substrate or well
 - Polysilicon Layers
 - Metal Interconnects
 - Contact: Metal to active
 - Via: Metal to metal
- 2. Intralayer Constraints
- 3. Interlayer Constraints

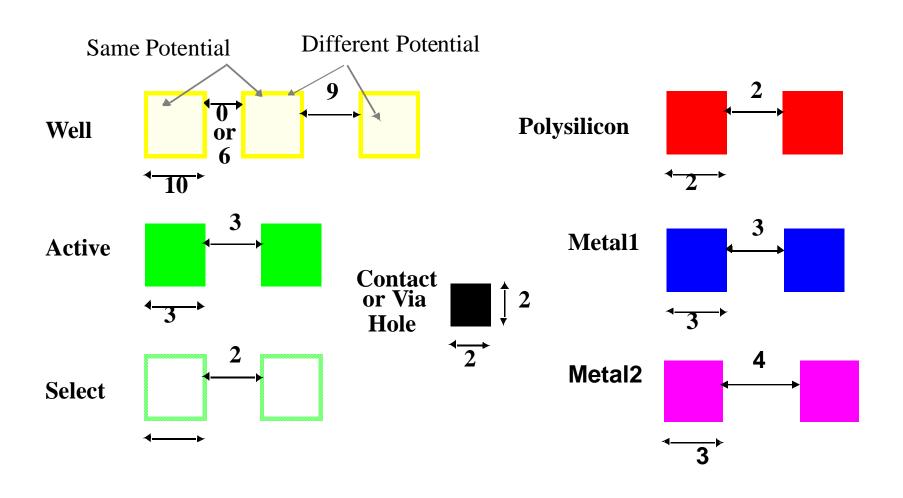
CMOS Process Layers

Layer	Color	Representation
Well (p,n)	Yellow	
Active Area (n+,p+)	Green	
Select (p+,n+)	Green	
Polysilicon	Red	
Metal1	Blue	
Metal2	Magenta	
Contact To Poly	Black	
Contact To Diffusion	Black	
Via	Black	

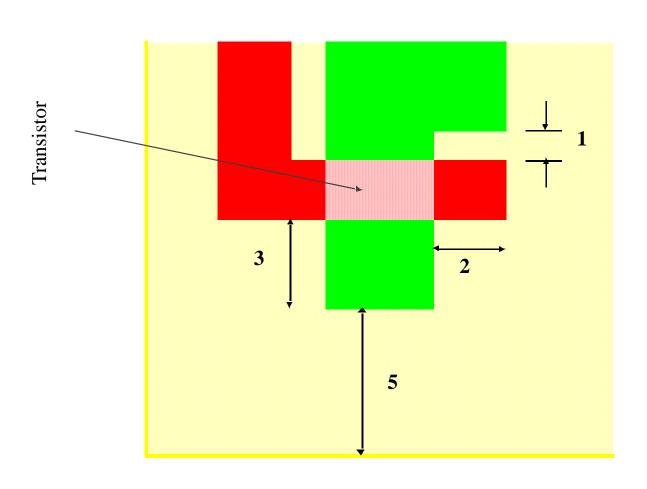
Layers in 0.25µm CMOS Process



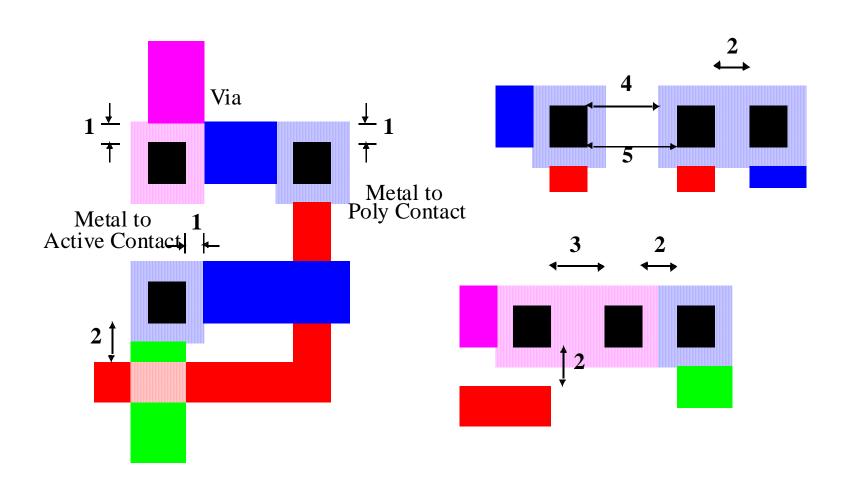
Intra-Layer Design Rules



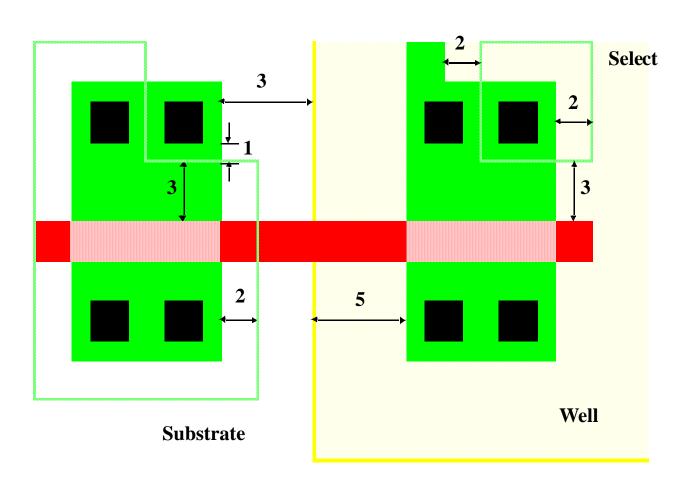
Single Transistor Layout



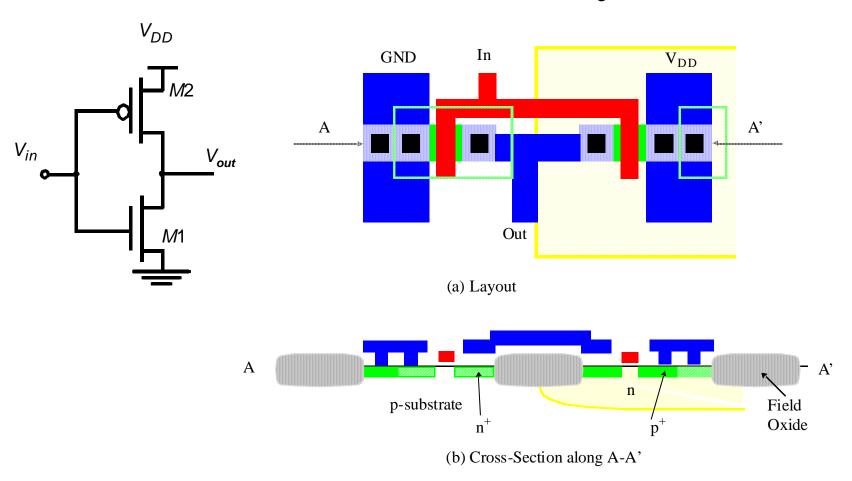
Vias and Contacts



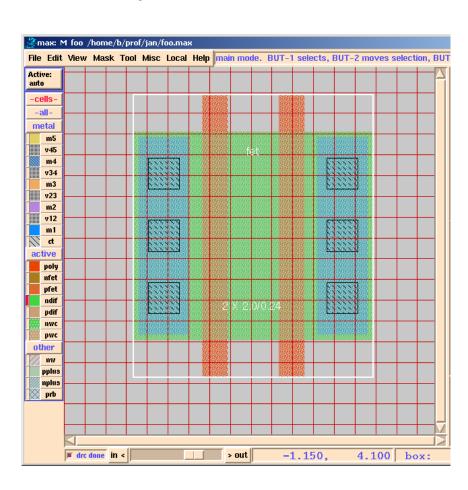
Select Layer



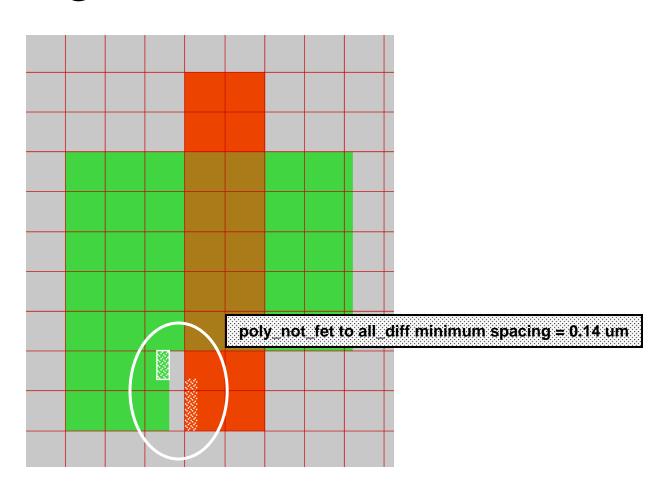
CMOS Inverter Layout



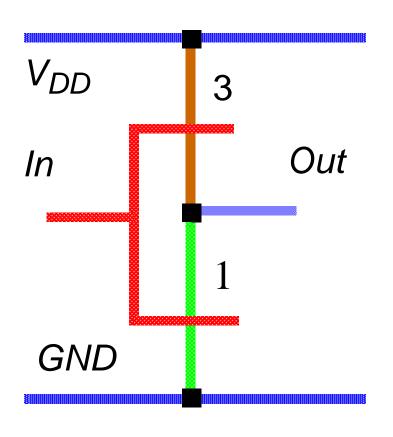
Layout Editor



Design Rule Checker



Stick Diagrams



- Dimensionless layout entities
- Only topology is important
- Final layout generated by "compaction" program (if available)

Stick diagram of an inverter